

Robert Kudrawiec

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315
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340
ext. papers

4,808
ext. citations

3.1
avg, IF

5.56
L-index

#	Paper	IF	Citations
315	Recent achievements in AMMONO-bulk method. <i>Journal of Crystal Growth</i> , 2010 , 312, 2499-2502	1.6	76
314	Recent Progress on 1.55- μm Dilute-Nitride Lasers. <i>IEEE Journal of Quantum Electronics</i> , 2007 , 43, 773-785	2	71
313	First-principles calculations of bismuth induced changes in the band structure of dilute Ga N Bi and In N Bi alloys: chemical trends versus experimental data. <i>Semiconductor Science and Technology</i> , 2015 , 30, 094001	1.8	70
312	High Bi content GaSbBi alloys. <i>Journal of Applied Physics</i> , 2014 , 116, 043511	2.5	60
311	Electronic Band Structure of Ga $\text{N}_x\text{PyAs}_{1-x-y}$ Highly Mismatched Alloys: Suitability for Intermediate-Band Solar Cells. <i>Physical Review Applied</i> , 2014 , 1,	4.3	60
310	Carrier localization in GaBiAs probed by photomodulated transmittance and photoluminescence. <i>Journal of Applied Physics</i> , 2009 , 106, 023518	2.5	54
309	Photoreflectance and contactless electroreflectance measurements of semiconductor structures by using bright and dark configurations. <i>Review of Scientific Instruments</i> , 2009 , 80, 096103	1.7	53
308	Explanation of annealing-induced blueshift of the optical transitions in GaInAsN/GaAs quantum wells. <i>Applied Physics Letters</i> , 2003 , 83, 2772-2774	3.4	53
307	The electronic band structure of Ge $_{1-x}\text{Sn}_x$ in the full composition range: indirect, direct, and inverted gaps regimes, band offsets, and the Burstein-Moss effect. <i>Journal Physics D: Applied Physics</i> , 2017 , 50, 195103	3	52
306	Development of GaInNAsSb alloys: Growth, band structure, optical properties and applications. <i>Physica Status Solidi (B): Basic Research</i> , 2007 , 244, 2707-2729	1.3	51
305	Application of contactless electroreflectance to III-nitrides. <i>Physica Status Solidi (B): Basic Research</i> , 2010 , 247, 1616-1621	1.3	48
304	Photoreflectance evidence of multiple band gaps in dilute GaInNAs layers lattice-matched to GaAs. <i>Journal of Applied Physics</i> , 2004 , 96, 2576-2579	2.5	47
303	Theoretical and experimental studies of electronic band structure for GaSb $_{1-x}\text{Bi}_x$ in the dilute Bi regime. <i>Journal Physics D: Applied Physics</i> , 2014 , 47, 355107	3	46
302	Experimental and theoretical studies of band gap alignment in GaAs $_{1-x}\text{Bi}_x$ /GaAs quantum wells. <i>Journal of Applied Physics</i> , 2014 , 116, 233508	2.5	46
301	Nonpolar GaN substrates grown by ammonothermal method. <i>Applied Physics Letters</i> , 2009 , 95, 131119	3.4	45
300	Band gap temperature-dependence of close-space sublimation grown Sb $_2$ Se $_3$ by photo-reflectance. <i>APL Materials</i> , 2018 , 6, 084901	5.7	45
299	Pressure coefficients for direct optical transitions in MoS $_2$, MoSe $_2$, WS $_2$, and WSe $_2$ crystals and semiconductor to metal transitions. <i>Scientific Reports</i> , 2016 , 6, 26663	4.9	44

298	Photoreflectance, photoluminescence, and microphotoluminescence study of optical transitions between delocalized and localized states in GaN _{0.02} As _{0.98} , Ga _{0.95} In _{0.05} N _{0.02} As _{0.98} , and GaN _{0.02} As _{0.90} Sb _{0.08} layers. <i>Physical Review B</i> , 2013 , 88,	3.3	44
297	Photoreflectance investigations of the energy level structure in GaInNAs-based quantum wells. <i>Journal of Physics Condensed Matter</i> , 2004 , 16, S3071-S3094	1.8	43
296	Temperature dependence of the band gap of GaSb _{1-x} Bix alloys with 0 < x < 1. <i>Applied Physics Letters</i> , 2013 , 103, 261907	3.4	40
295	Localized and delocalized states in GaNAs studied by microphotoluminescence and photoreflectance. <i>Applied Physics Letters</i> , 2009 , 94, 011907	3.4	40
294	Interband transitions in GaN _{0.02} As _{0.98} Sb _x GaAs (0 < x < 1). <i>Physical Review B</i> , 2006 , 73,	3.3	40
293	Material gain engineering in GeSn/Ge quantum wells integrated with an Si platform. <i>Scientific Reports</i> , 2016 , 6, 34082	4.9	39
292	Optically pumped 500 nm InGaN green lasers grown by plasma-assisted molecular beam epitaxy. <i>Journal of Applied Physics</i> , 2011 , 110, 063110	2.5	39
291	Combined Temperature and Pressure Sensing Using Luminescent NaBiF ₄ :Yb,Er Nanoparticles. <i>ACS Applied Nano Materials</i> , 2020 , 3, 4209-4217	5.6	38
290	Non-polar and semi-polar ammonothermal GaN substrates. <i>Semiconductor Science and Technology</i> , 2012 , 27, 024007	1.8	36
289	Contactless electromodulation spectroscopy of AlGaInGaN heterostructures with a two-dimensional electron gas: A comparison of photoreflectance and contactless electroreflectance. <i>Journal of Applied Physics</i> , 2006 , 100, 013501	2.5	36
288	Photoreflectance investigations of oscillator strength and broadening of optical transitions for GaAsSb _{1-x} InAs/GaAs bilayer quantum wells. <i>Applied Physics Letters</i> , 2004 , 84, 3453-3455	3.4	35
287	Influence of carrier localization on modulation mechanism in photoreflectance of GaAsN and GaInAsN. <i>Applied Physics Letters</i> , 2003 , 83, 1379-1381	3.4	35
286	Contactless electroreflectance and theoretical studies of band gap and spin-orbit splitting in InP _{1-x} Bix dilute bismide with 0 < x < 1. <i>Applied Physics Letters</i> , 2014 , 105, 222104	3.4	34
285	Interference effects in electromodulation spectroscopy applied to GaAs-based structures: A comparison of photoreflectance and contactless electroreflectance. <i>Applied Physics Letters</i> , 2005 , 86, 091115	3.4	33
284	Direct optical transitions at K- and H-point of Brillouin zone in bulk MoS ₂ , MoSe ₂ , WS ₂ , and WSe ₂ . <i>Journal of Applied Physics</i> , 2016 , 119, 235705	2.5	33
283	8-band and 14-band kp modeling of electronic band structure and material gain in Ga(In)AsBi quantum wells grown on GaAs and InP substrates. <i>Journal of Applied Physics</i> , 2015 , 118, 055702	2.5	32
282	GaNAsP: An intermediate band semiconductor grown by gas-source molecular beam epitaxy. <i>Applied Physics Letters</i> , 2013 , 102, 112105	3.4	32
281	Photoreflectance-probed excited states in InAs _{1-x} GaAlAs quantum dashes grown on InP substrate. <i>Applied Physics Letters</i> , 2006 , 89, 031908	3.4	32

280	Contactless electroreflectance study of E0 and E0 + π 0 transitions in In _{0.53} Ga _{0.47} Bi _x As _{1-x} alloys. <i>Applied Physics Letters</i> , 2011 , 99, 251906	3.4	31
279	On the deepness of contactless electroreflectance probing in semiconductor structures. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2007 , 204, 354-363	1.6	31
278	Nitrogen incorporation into strained (In, Ga) (As, N) thin films grown on (100), (511), (411), (311), and (111) GaAs substrates studied by photoreflectance spectroscopy and high-resolution x-ray diffraction. <i>Journal of Applied Physics</i> , 2006 , 100, 093522	2.5	30
277	Photomodulated reflectance and transmittance: optical characterisation of novel semiconductor materials and device structures. <i>Thin Solid Films</i> , 2004 , 450, 14-22	2.2	30
276	Electronic band structure of compressively strained Ge _{1-x} Sn _x with x . <i>Applied Physics Letters</i> , 2015 , 106, 142102	3.4	29
275	Contactless electroreflectance studies of Fermi level position on c-plane GaN surface grown by molecular beam epitaxy and metalorganic vapor phase epitaxy. <i>Applied Physics Letters</i> , 2012 , 100, 181603	3.4	29
274	Experimental investigation of the CMN matrix element in the band anticrossing model for GaAsN and GaInAsN layers. <i>Solid State Communications</i> , 2004 , 129, 353-357	1.6	29
273	Investigation of recombination processes involving defect-related states in (Ga,In)(As,Sb,N) compounds. <i>EPJ Applied Physics</i> , 2004 , 27, 313-316	1.1	29
272	Enhancement of Green Terbium-Related Photoluminescence from Highly Doped Microporous Alumina Xerogels in Mesoporous Anodic Alumina. <i>Journal of the Electrochemical Society</i> , 2002 , 149, H49	3.9	29
271	Photoacoustic and modulated reflectance studies of indirect and direct band gap in van der Waals crystals. <i>Scientific Reports</i> , 2017 , 7, 15365	4.9	28
270	Optically probed wetting layer in InAs/InGaAlAs/InP quantum-dash structures. <i>Applied Physics Letters</i> , 2005 , 86, 101904	3.4	28
269	The energy-fine structure of GaInNAs/GaAs multiple quantum wells grown at different temperatures and postgrown annealed. <i>Journal of Applied Physics</i> , 2004 , 96, 2909-2913	2.5	28
268	Improved optical quality of GaNAsSb in the dilute Sb limit. <i>Journal of Applied Physics</i> , 2005 , 97, 113510	2.5	28
267	Low- and high-energy photoluminescence from GaSb _{1-x} Bi _x with 0 . <i>Applied Physics Express</i> , 2014 , 7, 111202	2.4	27
266	The surface boundary conditions in GaN/AlGaN/GaN transistor heterostructures. <i>Applied Physics Letters</i> , 2011 , 98, 231902	3.4	27
265	Thermal quenching of single localized excitons in GaInNAs layers. <i>Applied Physics Letters</i> , 2011 , 98, 131903	3.1	26
264	Contactless electroreflectance of InGaN layers with indium content $\geq 6\%$: The surface band bending, band gap bowing, and Stokes shift issues. <i>Journal of Applied Physics</i> , 2009 , 106, 113517	2.5	26
263	Photoreflectance study of exciton energies and linewidths for homoepitaxial and heteroepitaxial GaN layers. <i>Journal of Applied Physics</i> , 2009 , 105, 093541	2.5	26

262	Contactless electroreflectance of GaN _y As _{1-y} /GaAs multi quantum wells: The conduction band offset and electron effective mass issues. <i>Solid State Communications</i> , 2006 , 138, 365-370	1.6	26
261	Phase-Transition-Induced Carrier Mass Enhancement in 2D Ruddlesden-Popper Perovskites. <i>ACS Energy Letters</i> , 2019 , 4, 2386-2392	20.1	25
260	Optical properties of GaAsBi/GaAs quantum wells: Photorefectance, photoluminescence and time-resolved photoluminescence study. <i>Semiconductor Science and Technology</i> , 2015 , 30, 094005	1.8	25
259	Contactless electroreflectance spectroscopy of optical transitions in low dimensional semiconductor structures. <i>Opto-electronics Review</i> , 2012 , 20,	2.4	25
258	Photorefectance spectroscopy of semiconductor structures at hydrostatic pressure: A comparison of GaInAs/GaAs and GaInNAs/GaAs single quantum wells. <i>Applied Surface Science</i> , 2006 , 253, 80-84	6.7	25
257	Pressure dependence of direct optical transitions in ReS ₂ and ReSe ₂ . <i>Npj 2D Materials and Applications</i> , 2019 , 3,	8.8	24
256	Alloying of GaN _x As _{1-x} with InN _x As _{1-x} : A simple formula for the band gap parametrization of Ga _{1-y} In _y N _x As _{1-x} alloys. <i>Journal of Applied Physics</i> , 2007 , 101, 023522	2.5	24
255	The nature of optical transitions in Ga _{0.64} In _{0.36} As _{1-x} N _x /GaAs single quantum wells with low nitrogen content (x=0.008). <i>Solid State Communications</i> , 2003 , 127, 613-618	1.6	24
254	Band structure and the optical gain of GaInNAs/GaAs quantum wells modeled within 10-band and 8-band kp model. <i>Journal of Applied Physics</i> , 2013 , 113, 063514	2.5	23
253	Raman scattering by the E _{2h} and A ₁ (LO) phonons of In _x Ga _{1-x} N epilayers (0.25 <i>Journal of Applied Physics</i> , 2012 , 111, 063502	2.5	23
252	Photoluminescence investigation of europium-doped alumina, titania and indium sol-gel-derived films in porous anodic alumina. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2003 , 105, 53-56	3.1	23
251	Electronic band structure and material gain of III-V-Bi quantum wells grown on GaSb substrate and dedicated for mid-infrared spectral range. <i>Journal of Applied Physics</i> , 2016 , 119, 075701	2.5	23
250	Carrier dynamics between delocalized and localized states in type-II GaAsSb/GaAs quantum wells. <i>Applied Physics Letters</i> , 2011 , 98, 061910	3.4	22
249	Band gap discontinuity in Ga _{0.9} In _{0.1} N _{0.027} As _{0.973-x} Sb _x /GaAs single quantum wells with 0?x. <i>Applied Physics Letters</i> , 2006 , 88, 221113	3.4	22
248	Photoluminescence investigation of porous anodic alumina with spin-on europium-containing titania sol-gel films. <i>Journal of Alloys and Compounds</i> , 2002 , 341, 211-213	5.7	21
247	Electromodulation spectroscopy of direct optical transitions in Ge _{1-x} Sn _x layers under hydrostatic pressure and built-in strain. <i>Journal of Applied Physics</i> , 2016 , 119, 215703	2.5	21
246	Contactless electroreflectance study of the Fermi level pinning on GaSb surface in n-type and p-type GaSb Van Hoof structures. <i>Journal of Applied Physics</i> , 2012 , 112, 123513	2.5	20
245	Photorefectance study of the energy gap and spin-orbit splitting in InNAs alloys. <i>Applied Physics Letters</i> , 2009 , 94, 151902	3.4	20

244	Band-gap discontinuity in GaN _{0.02} As _{0.87} Sb _{0.11} /GaAs single-quantum wells investigated by photoreflectance spectroscopy. <i>Applied Physics Letters</i> , 2005 , 86, 141908	3.4	20
243	Contactless electroreflectance studies of the Fermi level position at the air/GaN interface: Bistable nature of the Ga-polar surface. <i>Applied Surface Science</i> , 2017 , 396, 1657-1666	6.7	19
242	Optical absorption and thermal conductivity of GaAsPN absorbers grown on GaP in view of their use in multijunction solar cells. <i>Solar Energy Materials and Solar Cells</i> , 2015 , 141, 291-298	6.4	19
241	Band anticrossing in ZnOSe highly mismatched alloy. <i>Applied Physics Express</i> , 2014 , 7, 071202	2.4	19
240	Development of dilute nitride materials for mid-infrared diode lasers. <i>Semiconductor Science and Technology</i> , 2012 , 27, 094009	1.8	19
239	Built-in electric field and large Stokes shift in near-lattice-matched GaN/AlInN quantum wells. <i>Applied Physics Letters</i> , 2008 , 92, 201901	3.4	19
238	1.54 eV photoluminescence from Er-doped sol-gel derived In ₂ O ₃ films embedded in porous anodic alumina. <i>Optical Materials</i> , 2006 , 28, 685-687	3.3	19
237	Exfoliated CrPS with Promising Photoconductivity. <i>Small</i> , 2020 , 16, e1905924	11	19
236	Correlations between the band structure, activation energies of electron traps, and photoluminescence in n-type GaNAs layers. <i>Applied Physics Letters</i> , 2012 , 101, 082109	3.4	18
235	Investigations of GaN surface quantum well in AlGaIn/GaN transistor heterostructures by contactless electroreflectance spectroscopy. <i>Applied Physics Letters</i> , 2006 , 89, 231912	3.4	18
234	Fermi level and bands offsets determination in insulating (Ga,Mn)N/GaN structures. <i>Scientific Reports</i> , 2017 , 7, 41877	4.9	17
233	Deep-level defects in n-type GaAsBi alloys grown by molecular beam epitaxy at low temperature and their influence on optical properties. <i>Scientific Reports</i> , 2017 , 7, 12824	4.9	17
232	Exciton Binding Energy of Two-Dimensional Highly Luminescent Colloidal Nanostructures Determined from Combined Optical and Photoacoustic Spectroscopies. <i>Journal of Physical Chemistry Letters</i> , 2019 , 10, 3459-3464	6.4	17
231	Contactless electroreflectance studies of surface potential barrier for N- and Ga-face epilayers grown by molecular beam epitaxy. <i>Applied Physics Letters</i> , 2013 , 103, 052107	3.4	17
230	Structural and Optical Properties of Semipolar GaN Substrates Obtained by Ammonothermal Method. <i>Applied Physics Express</i> , 2010 , 3, 101001	2.4	17
229	Atomic arrangement and emission properties of GaAs(In, Sb)N quantum wells. <i>Semiconductor Science and Technology</i> , 2009 , 24, 075013	1.8	17
228	Model of hopping excitons in GaInNAs: simulations of sharp lines in micro-photoluminescence spectra and their dependence on the excitation power and temperature. <i>Journal of Physics Condensed Matter</i> , 2011 , 23, 205804	1.8	17
227	Photoreflectance and photoluminescence study of Ga _{0.76} In _{0.24} Sb/GaSb single quantum wells: Band structure and thermal quenching of photoluminescence. <i>Journal of Applied Physics</i> , 2008 , 103, 113514	2.5	17

226	On the modulation mechanisms in photoreflectance of an ensemble of self-assembled InAs/GaAs quantum dots. <i>Journal of Applied Physics</i> , 2006 , 100, 073502	2.5	17
225	Contactless electroreflectance approach to study the Fermi level position in GaInNAs/GaAs quantum wells. <i>Journal of Applied Physics</i> , 2007 , 102, 113501	2.5	17
224	Beyond Quantum Efficiency Limitations Originating from the Piezoelectric Polarization in Light-Emitting Devices. <i>ACS Photonics</i> , 2019 , 6, 1963-1971	6.3	16
223	Temperature dependence of photoluminescence from InNAsSb layers: The role of localized and free carrier emission in determination of temperature dependence of energy gap. <i>Applied Physics Letters</i> , 2013 , 102, 122109	3.4	16
222	Dynamics of localized excitons in Ga _{0.69} In _{0.31} N _{0.015} As _{0.985} /GaAs quantum well: Experimental studies and Monte-Carlo simulations. <i>Applied Physics Letters</i> , 2012 , 100, 202105	3.4	16
221	Photoreflectance of InN and InN:Mg layers: An evidence of Fermi level shift toward the valence band upon Mg doping in InN. <i>Applied Physics Letters</i> , 2008 , 93, 131917	3.4	16
220	Temperature evolution of carrier dynamics in GaN _x PyAs _{1-x} alloys. <i>Journal of Applied Physics</i> , 2015 , 117, 175702	2.5	15
219	Transparency of GaN substrates in the mid-infrared spectral range. <i>Crystal Research and Technology</i> , 2012 , 47, 347-350	1.3	15
218	Photoreflectance study of N- and Sb-related modifications of the energy gap and spin-orbit splitting in InNAsSb alloys. <i>Applied Physics Letters</i> , 2011 , 99, 011904	3.4	15
217	Room temperature contactless electroreflectance characterization of InGaAs/InAs/GaAs quantum dot wafers. <i>Semiconductor Science and Technology</i> , 2006 , 21, 1402-1407	1.8	15
216	Band structure of germanium carbides for direct bandgap silicon photonics. <i>Journal of Applied Physics</i> , 2016 , 120, 053102	2.5	15
215	Effects of a semiconductor matrix on the band anticrossing in dilute group II-VI oxides. <i>Semiconductor Science and Technology</i> , 2015 , 30, 085018	1.8	14
214	Surface photovoltage and modulation spectroscopy of E ₁ and E ₁ + ΔE transitions in GaNAs layers. <i>Thin Solid Films</i> , 2014 , 567, 101-104	2.2	14
213	Theoretical studies of the influence of structural inhomogeneities on the radiative recombination time in polar InGaN quantum wells. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2012 , 209, 752-760	1.6	14
212	Temperature dependence of E ₀ and E ₀ + ΔE transitions in In _{0.53} Ga _{0.47} Bi _x As _{1-x} alloys studied by photoreflectance. <i>Journal of Applied Physics</i> , 2012 , 112, 113508	2.5	14
211	Room temperature contactless electroreflectance of the ground and excited state transitions in Ga _{0.76} In _{0.24} As _{0.08} Sb _{0.92} /GaSb single quantum wells of various widths. <i>Applied Physics Letters</i> , 2008 , 92, 041910	3.4	14
210	Infrared photomodulation spectroscopy of an In _{0.22} Ga _{0.78} Sb/GaSb single quantum well. <i>Superlattices and Microstructures</i> , 2002 , 32, 19-23	2.8	14
209	Photoreflectance and photoluminescence investigations of a step-like GaInNAsSb/GaAsN/GaAs quantum well tailored at 1.5 μm: The energy level structure and the Stokes shift. <i>Journal of Applied Physics</i> , 2005 , 97, 053515	2.5	14

208	Photoacoustic spectroscopy of absorption edge for GaAsBi/GaAs nanowires grown on Si substrate. <i>Applied Physics Letters</i> , 2016 , 109, 182106	3.4	14
207	Type I GaSb _{1-x} Bi _x /GaSb quantum wells dedicated for mid infrared laser applications: Photoreflectance studies of bandgap alignment. <i>Journal of Applied Physics</i> , 2019 , 125, 205706	2.5	13
206	Structural and optical properties of GaSbBi/GaSb quantum wells [Invited]. <i>Optical Materials Express</i> , 2018 , 8, 893	2.6	13
205	Influence of non-radiative recombination on photoluminescence decay time in GaInNAs quantum wells with Ga- and In-rich environments of nitrogen atoms. <i>Journal of Applied Physics</i> , 2012 , 111, 063514	2.5	13
204	Screening effect in contactless electroreflectance spectroscopy observed for AlGaIn/GaN heterostructures with two dimensional electron gas. <i>Thin Solid Films</i> , 2007 , 515, 4662-4665	2.2	13
203	Energy difference between electron subbands in AlInN/GaN quantum wells studied by contactless electroreflectance spectroscopy. <i>Applied Physics Letters</i> , 2006 , 89, 251908	3.4	13
202	Photoreflectance investigation of InAs quantum dashes embedded in In _{0.53} Ga _{0.47} As/In _{0.53} Ga _{0.23} Al _{0.24} As quantum well grown on InP substrate. <i>Applied Physics Letters</i> , 2006 , 88, 141915	3.4	13
201	Photoreflectance investigations of a donor-related transition in AlGaIn/GaN transistor structures. <i>Applied Physics Letters</i> , 2005 , 87, 153502	3.4	13
200	Direct and indirect optical transitions in bulk and atomically thin MoS ₂ studied by photoreflectance and photoacoustic spectroscopy. <i>Journal of Applied Physics</i> , 2019 , 125, 135701	2.5	12
199	Ammonothermal growth of GaN crystals on HVPE-GaN seeds prepared with the use of ammonothermal substrates. <i>Journal of Crystal Growth</i> , 2015 , 427, 1-6	1.6	12
198	Bi-induced acceptor level responsible for partial compensation of native free electron density in In _{0.15} P _{0.85} Bi dilute bismide alloys. <i>Journal Physics D: Applied Physics</i> , 2016 , 49, 115107	3	12
197	Electromodulation spectroscopy of highly mismatched alloys. <i>Journal of Applied Physics</i> , 2019 , 126, 141103	3	12
196	Theoretical studies of optical gain tuning by hydrostatic pressure in GaInNAs/GaAs quantum wells. <i>Journal of Applied Physics</i> , 2014 , 115, 033515	2.5	12
195	Contactless electroreflectance of GaN bulk crystals grown by ammonothermal method and GaN epilayers grown on these crystals. <i>Applied Physics Letters</i> , 2008 , 93, 061910	3.4	12
194	Three beam photoreflectance as a powerful method to investigate semiconductor heterostructures. <i>Thin Solid Films</i> , 2004 , 450, 71-74	2.2	12
193	Luminescence of Eu ³⁺ and Tb ³⁺ Ions in the Structure Microporous Xerogel/Mesoporous Anodic Aluminum Oxide. <i>Journal of Applied Spectroscopy</i> , 2003 , 70, 59-64	0.7	12
192	Multicolor emission from intermediate band semiconductor ZnOSe. <i>Scientific Reports</i> , 2017 , 7, 44214	4.9	11
191	Nitrogen-related changes in exciton localization and dynamics in GaInNAs/GaAs quantum wells grown by metalorganic vapor phase epitaxy. <i>Applied Physics A: Materials Science and Processing</i> , 2015 , 118, 479-486	2.6	11

190	Bandgap engineering in III-nitrides with boron and group V elements: Toward applications in ultraviolet emitters. <i>Applied Physics Reviews</i> , 2020 , 7, 041314	17.3	11
189	Hidden spin-polarized bands in semiconducting 2H-MoTe ₂ . <i>Materials Research Letters</i> , 2020 , 8, 75-81	7.4	11
188	Time-resolved photoluminescence studies of annealed 1.3- μm GaInNAsSb quantum wells. <i>Nanoscale Research Letters</i> , 2014 , 9, 81	5	11
187	Nitrogen-related intermediate band in P-rich GaNPAs alloys. <i>Scientific Reports</i> , 2017 , 7, 15703	4.9	11
186	Contactless electroreflectance studies of free exciton binding energy in Zn _{1-x} Mg _x O epilayers. <i>Applied Physics Letters</i> , 2013 , 103, 251908	3.4	11
185	Growth and characterization of InGaN for photovoltaic devices. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011 , 8, 2460-2462		11
184	Growth of GaN epilayers on c-, m-, a-, and (20.1)-plane GaN bulk substrates obtained by ammonothermal method. <i>Journal of Crystal Growth</i> , 2011 , 328, 5-12	1.6	11
183	Correlation between the optical quality and the Fermi level position in GaInNAs alloys. <i>Journal Physics D: Applied Physics</i> , 2008 , 41, 245107	3	11
182	Photoreflectance and contactless electroreflectance spectroscopy of GaAs-based structures: The below band gap oscillation features. <i>Applied Surface Science</i> , 2006 , 253, 266-270	6.7	11
181	Contactless electroreflectance of GaInNAsSb/GaAs single quantum wells with indium content of 8% \leq 2%. <i>Journal of Applied Physics</i> , 2007 , 101, 013504	2.5	11
180	Ground and excited state transitions in as-grown Ga _{0.64} In _{0.36} N _{0.046} As _{0.954} quantum wells studied by contactless electroreflectance. <i>Applied Physics Letters</i> , 2007 , 90, 041916	3.4	11
179	Optical properties of GaInNAs/GaAs quantum wells: character of optical transitions and carrier localisation effect. <i>Physica Status Solidi A</i> , 2004 , 201, 364-367		11
178	Determination of dislocation density in GaN/sapphire layers using XRD measurements carried out from the edge of the sample. <i>Journal of Alloys and Compounds</i> , 2020 , 825, 153838	5.7	10
177	Identification of nitrogen- and host-related deep-level traps in n-type GaNAs and their evolution upon annealing. <i>Journal of Applied Physics</i> , 2014 , 116, 013705	2.5	10
176	Photoreflectance spectroscopy of GaInSbBi and AlGaSbBi quaternary alloys. <i>Applied Physics Letters</i> , 2014 , 105, 112102	3.4	10
175	Surface properties of c-plane GaN grown by plasma-assisted molecular beam epitaxy. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2013 , 31, 03C112	1.3	10
174	Properties of truly bulk GaN monocrystals grown by ammonothermal method. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009 , 6, 2661-2664		10
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